

Mohammed Zeghouane

List of Publications by Year in descending order

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12
papers

73
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1683354

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docs citations

12
times ranked

111
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhancing the incorporation of Sn in vapor-liquid-solid GeSn nanowires by modulation of the droplet composition. <i>Nanotechnology</i> , 2022, 33, 245605.	1.3	0
2	Long catalyst-free InAs nanowires grown on silicon by HVPE. <i>CrystEngComm</i> , 2021, 23, 378-384.	1.3	4
3	Thermodynamics of the Vapor-Liquid-Solid Growth of Ternary III-V Nanowires in the Presence of Silicon. <i>Nanomaterials</i> , 2021, 11, 83.	1.9	0
4	Selective Area Growth by Hydride Vapor Phase Epitaxy and Optical Properties of InAs Nanowire Arrays. <i>Crystal Growth and Design</i> , 2021, 21, 5158-5163.	1.4	5
5	Comprehensive model toward optimization of SAG In-rich InGaN nanorods by hydride vapor phase epitaxy. <i>Nanotechnology</i> , 2021, 32, 155601.	1.3	0
6	Impact of droplet composition on the nucleation rate and morphology of vapor-liquid-solid GeSn nanowires. <i>Nanotechnology</i> , 2020, 31, 405602.	1.3	5
7	Formation of voids in selective area growth of InN nanorods in SiN _x on GaN templates. <i>Nano Futures</i> , 2020, 4, 025002.	1.0	5
8	Morphological Control of InN Nanorods by Selective Area Growth-Hydride Vapor-Phase Epitaxy. <i>Crystal Growth and Design</i> , 2020, 20, 2232-2239.	1.4	5
9	Selective growth of ordered hexagonal InN nanorods. <i>CrystEngComm</i> , 2019, 21, 2702-2708.	1.3	13
10	Compositional control of homogeneous InGaN nanowires with the In content up to 90%. <i>Nanotechnology</i> , 2019, 30, 044001.	1.3	12
11	Growth of Ge _{1-x} Sn _x Nanowires by Chemical Vapor Deposition via Vapor-Liquid-Solid Mechanism Using GeH ₄ and SnCl ₄ . <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700743.	0.8	18
12	Crystal engineering by tuning the growth kinetics of GaN 3-D microstructures in SAG-HVPE. <i>CrystEngComm</i> , 2018, 20, 6207-6213.	1.3	6